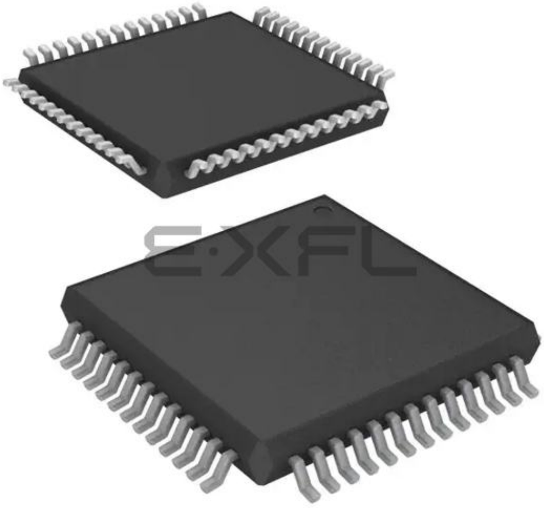
Renesas Electronics America Inc - R5F100JGGFA#X0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100jggfa-x0

Email: info@E-XFL.COM

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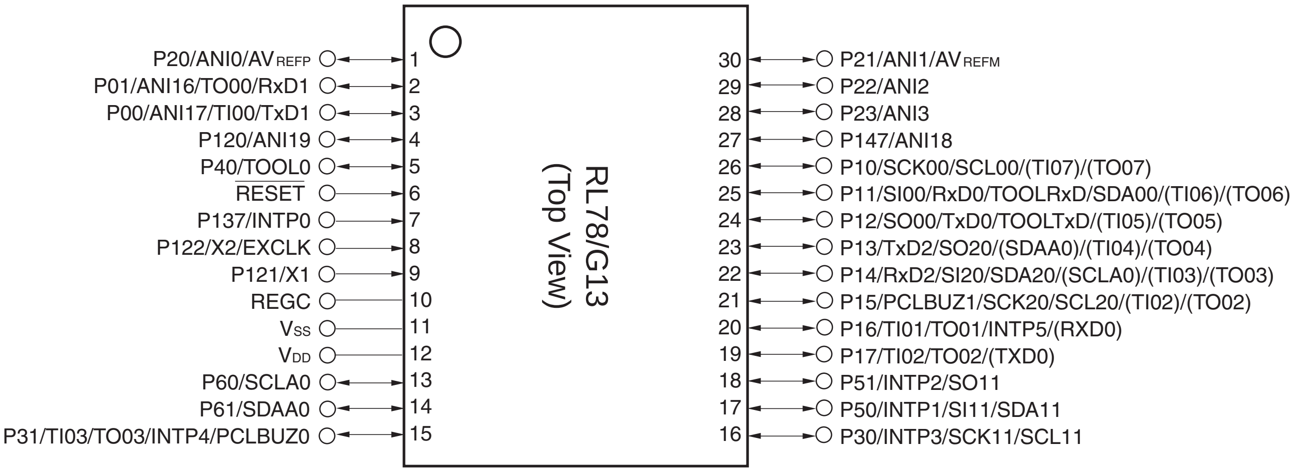
1.3.4 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

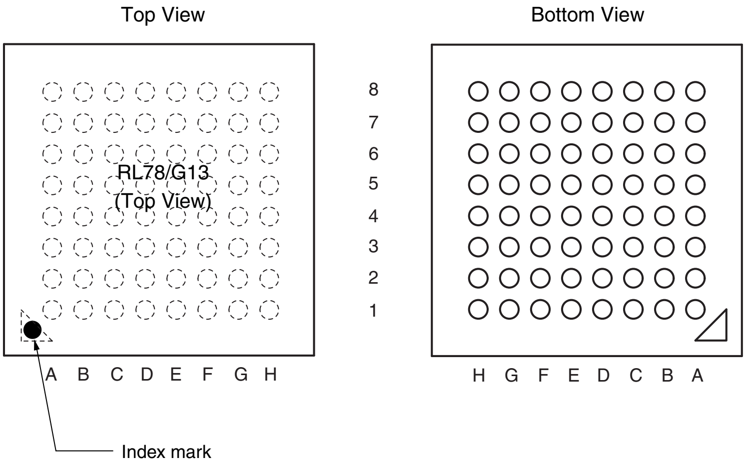


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

- 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/(SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ/SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20/(SCLA0)/(TI03)/(TO03)	G2	P25/ANI5
A3	P70/KR0/SCK21/SCL21	C3	P74/KR4/INTP8/SI01/SDA01	E3	P15/SCK20/SCL20/(TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9/SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5/(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/(TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1/SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	V_{SS}	E7	$\overline{\text{RESET}}$	G7	P00/TI00
A8	EV_{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11/SDA11	D1	P55/(PCLBUZ1)/(SCK00)	F1	P10/SCK00/SCL00/(TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0/TOOLRxD/SDA00/(TI06)/(TO06)	H2	P27/ANI7
B3	P73/KR3/SO01	D3	P17/TI02/TO02/(SO00)/(TxD0)	F3	P12/SO00/TxD0/TOOLTxD/(INTP5)/(TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/(RxD2)	D4	P54	F4	P21/ANI1/AV_{REFM}	H4	P23/ANI3
B5	P31/TI03/TO03/INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AV_{REFP}
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V_{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EV_{SS0}	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EV_{SS0} pin the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.

3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.

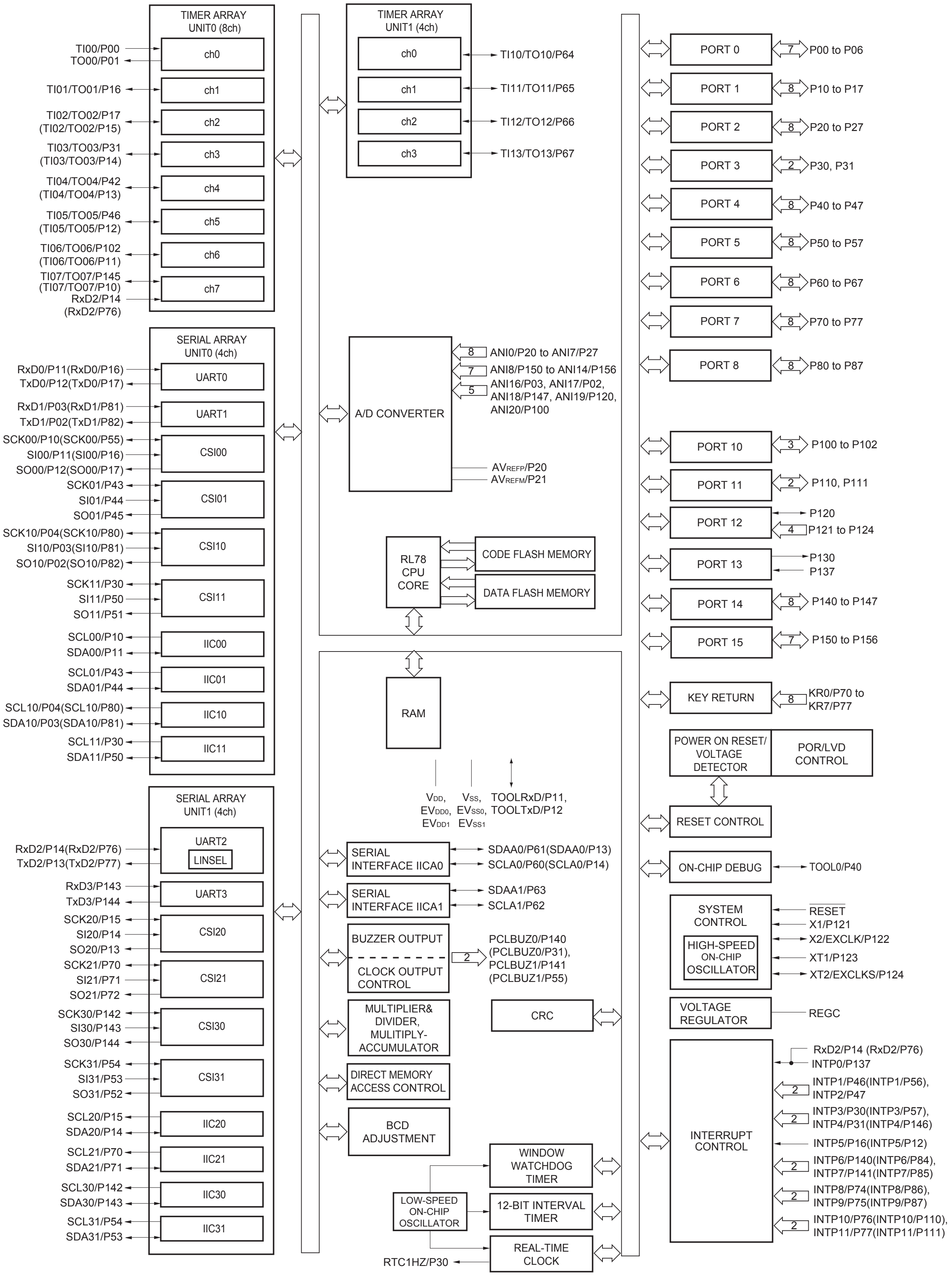
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.4 Pin Identification

ANI0 to ANI14, ANI16 to ANI26:	Analog input
AV_{REFM}:	A/D converter reference potential (– side) input
AV_{REFP}:	A/D converter reference potential (+ side) input
EV_{DD0}, EV_{DD1}:	Power supply for port
EV_{SS0}, EV_{SS1}:	Ground for port
EXCLK:	External clock input (Main system clock)
EXCLKS:	External clock input (Subsystem clock)
INTP0 to INTP11:	Interrupt request from peripheral
KR0 to KR7:	Key return
P00 to P07:	Port 0
P10 to P17:	Port 1
P20 to P27:	Port 2
P30 to P37:	Port 3
P40 to P47:	Port 4
P50 to P57:	Port 5
P60 to P67:	Port 6
P70 to P77:	Port 7
P80 to P87:	Port 8
P90 to P97:	Port 9
P100 to P106:	Port 10
P110 to P117:	Port 11
P120 to P127:	Port 12
P130, P137:	Port 13
P140 to P147:	Port 14
P150 to P156:	Port 15
PCLBUZ0, PCLBUZ1:	Programmable clock output/buzzer output

REGC:	Regulator capacitance
$\overline{\text{RESET}}$:	Reset
RTC1HZ:	Real-time clock correction clock (1 Hz) output
RxD0 to RxD3:	Receive data
SCK00, SCK01, SCK10, SCK11, SCK20, SCK21, SCLA0, SCLA1:	Serial clock input/output
SCLA0, SCLA1, SCL00, SCL01, SCL10, SCL11, SCL20,SCL21, SCL30, SCL31:	Serial clock output
SDAA0, SDAA1, SDA00, SDA01,SDA10, SDA11, SDA20,SDA21, SDA30, SDA31:	Serial data input/output
SI00, SI01, SI10, SI11, SI20, SI21, SI30, SI31:	Serial data input
SO00, SO01, SO10, SO11, SO20, SO21, SO30, SO31:	Serial data output
TI00 to TI07, TI10 to TI17:	Timer input
TO00 to TO07, TO10 to TO17:	Timer output
TOOL0:	Data input/output for tool
TOOLRxD, TOOLTxD:	Data input/output for external device
TxD0 to TxD3:	Transmit data
V_{DD}:	Power supply
V_{SS}:	Ground
X1, X2:	Crystal oscillator (main system clock)
XT1, XT2:	Crystal oscillator (subsystem clock)

1.5.13 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −10.0 mA	EV_{DD0} − 1.5			V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −3.0 mA	EV_{DD0} − 0.7			V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −2.0 mA	EV_{DD0} − 0.6			V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −1.5 mA	EV_{DD0} − 0.5			V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OH1} = −1.0 mA	EV_{DD0} − 0.5			V
	V_{OH2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = −100 μA	V_{DD} − 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD2}[Note 2]	HALT mode	HS (high-speed main) mode[Note 7]	f_{IH} = 32 MHz[Note 4]	V_{DD} = 5.0 V		0.54	1.63	mA
					V_{DD} = 3.0 V		0.54	1.63	mA
				f_{IH} = 24 MHz[Note 4]	V_{DD} = 5.0 V		0.44	1.28	mA
					V_{DD} = 3.0 V		0.44	1.28	mA
				f_{IH} = 16 MHz[Note 4]	V_{DD} = 5.0 V		0.40	1.00	mA
					V_{DD} = 3.0 V		0.40	1.00	mA
			LS (low-speed main) mode[Note 7]	f_{IH} = 8 MHz[Note 4]	V_{DD} = 3.0 V		260	530	µA
					V_{DD} = 2.0 V		260	530	µA
			LV (low-voltage main) mode[Note 7]	f_{IH} = 4 MHz[Note 4]	V_{DD} = 3.0 V		420	640	µA
					V_{DD} = 2.0 V		420	640	µA
			HS (high-speed main) mode[Note 7]	f_{MX} = 20 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		0.28	1.00	mA
					Resonator connection		0.45	1.17	mA
				f_{MX} = 20 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		0.28	1.00	mA
					Resonator connection		0.45	1.17	mA
				f_{MX} = 10 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		0.19	0.60	mA
					Resonator connection		0.26	0.67	mA
				f_{MX} = 10 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		0.19	0.60	mA
					Resonator connection		0.26	0.67	mA
			LS (low-speed main) mode[Note 7]	f_{MX} = 8 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		95	330	µA
					Resonator connection		145	380	µA
				f_{MX} = 8 MHz[Note 3], V_{DD} = 2.0 V	Square wave input		95	330	µA
					Resonator connection		145	380	µA
			Subsystem clock operation	f_{SUB} = 32.768 kHz[Note 5] T_A = –40°C	Square wave input		0.25	0.57	µA
					Resonator connection		0.44	0.76	µA
				f_{SUB} = 32.768 kHz[Note 5] T_A = +25°C	Square wave input		0.30	0.57	µA
					Resonator connection		0.49	0.76	µA
				f_{SUB} = 32.768 kHz[Note 5] T_A = +50°C	Square wave input		0.37	1.17	µA
					Resonator connection		0.56	1.36	µA
				f_{SUB} = 32.768 kHz[Note 5] T_A = +70°C	Square wave input		0.53	1.97	µA
					Resonator connection		0.72	2.16	µA
				f_{SUB} = 32.768 kHz[Note 5] T_A = +85°C	Square wave input		0.82	3.37	µA
					Resonator connection		1.01	3.56	µA
	I_{DD3}[Note 6]	STOP mode[Note 8]	T_A = –40°C				0.18	0.50	µA
			T_A = +25°C				0.23	0.50	µA
			T_A = +50°C				0.30	1.10	µA
			T_A = +70°C				0.46	1.90	µA
			T_A = +85°C				0.75	3.30	µA

(**Notes** and **Remarks** are listed on the next page.)

Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$

$1.8 \text{ V} \leq EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

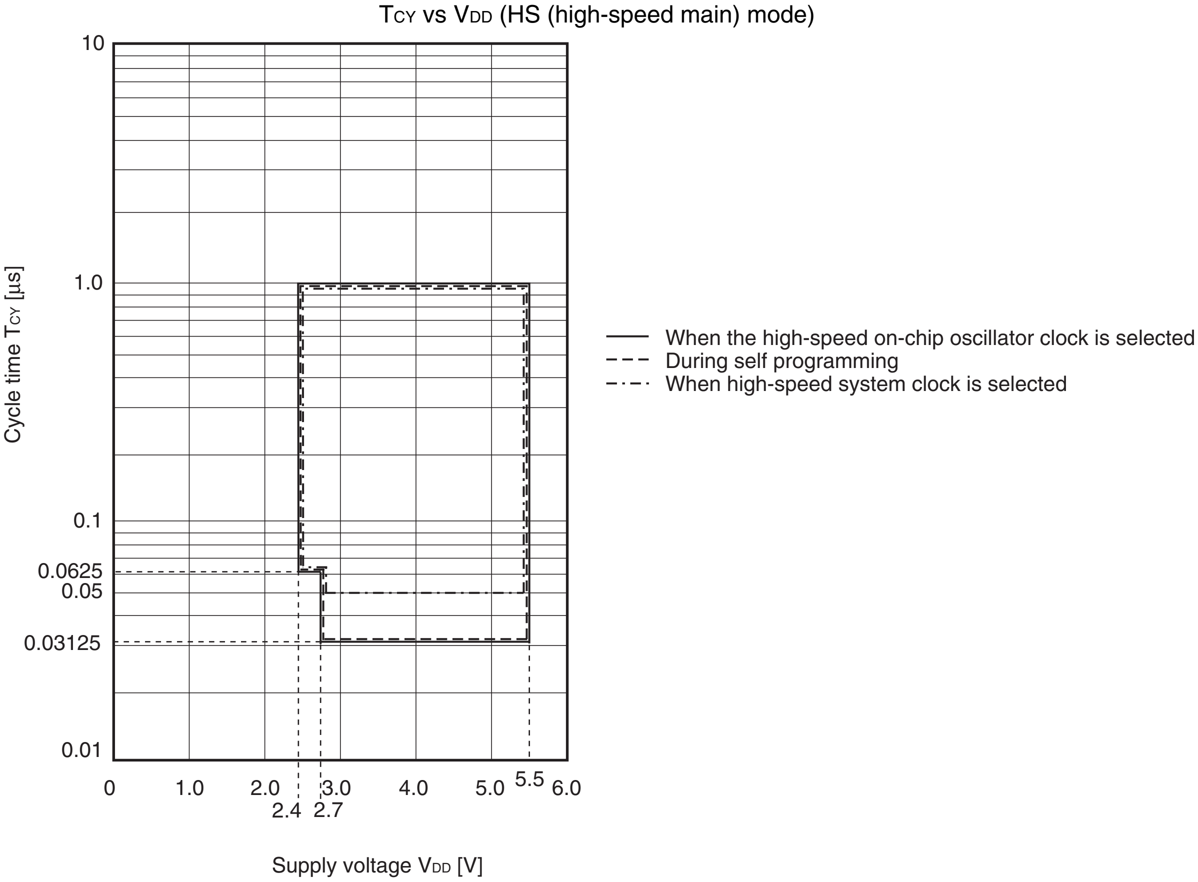
$1.6 \text{ V} \leq EV_{DD0} < 1.8 \text{ V}$: MIN. 250 ns

Remark f_{MCK}: Timer array unit operation clock frequency

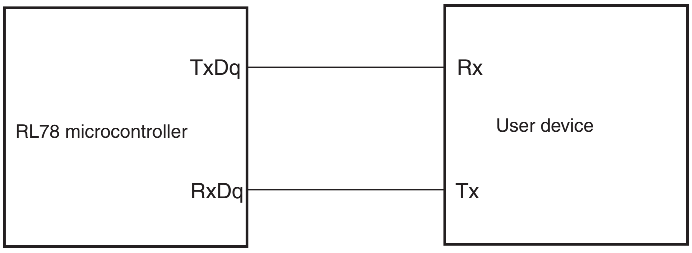
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

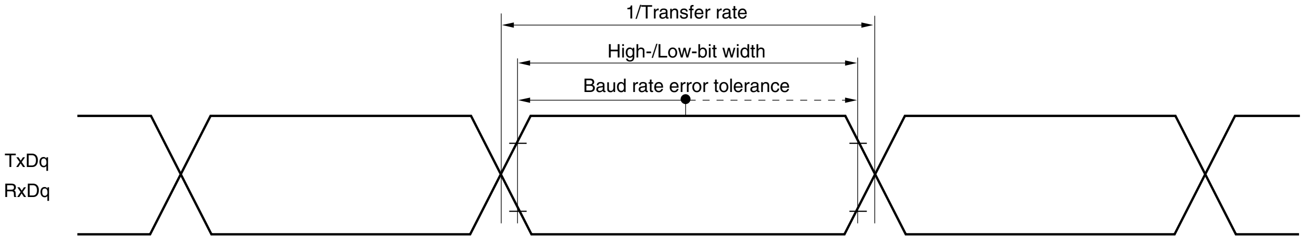
Minimum Instruction Execution Time during Main System Clock Operation



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

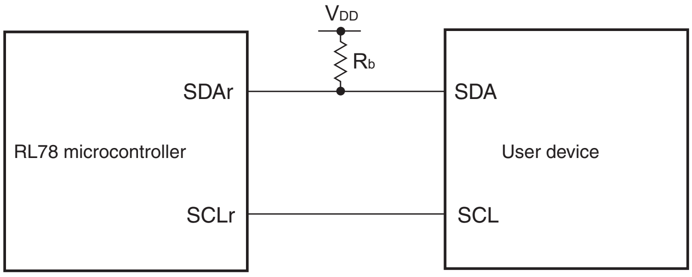
(5) During communication at same potential (simplified I^2C mode) (1/2)

(T_A = −40 to +85°C, 1.6 V ≤ $EV_{DD0} = EV_{DD1} \leq V_{DD} \leq$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V)

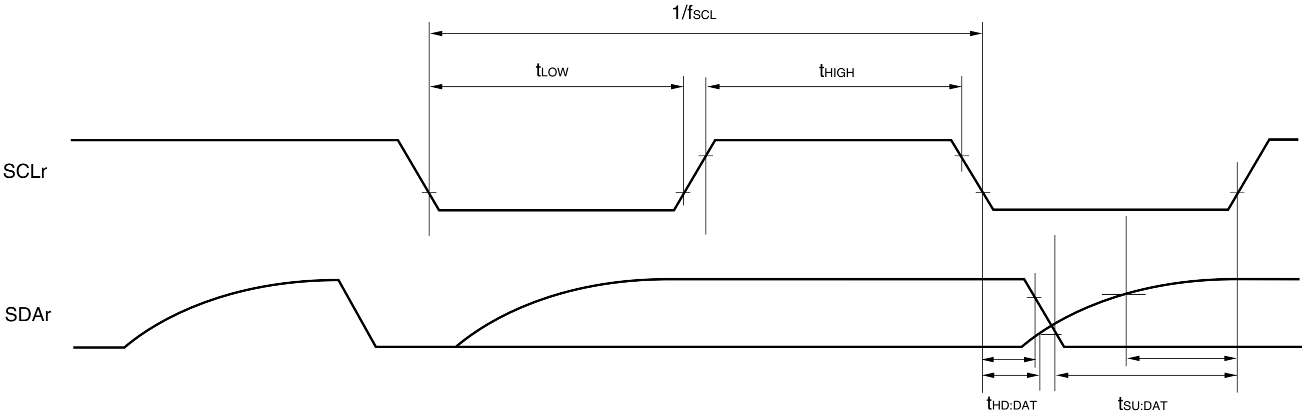
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		1850		1850		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		1850		1850		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

Simplified I^{2}C mode mode connection diagram (during communication at same potential)



Simplified I^{2}C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			**Note 1**		**Note 1**		**Note 1**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			**Note 3**		**Note 3**		**Note 3**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			**Notes 5, 6**		**Notes 5, 6**		**Notes 5, 6**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Notes 1. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7\ V \leq EV_{DD0} < 4.0\ V$ and $2.3\ V \leq V_b \leq 2.7\ V$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

5. Use it with $EV_{DD0} \geq V_b$.

6. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $1.8\ V \leq EV_{DD0} < 3.3\ V$ and $1.6\ V \leq V_b \leq 2.0\ V$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3}\ [\text{bps}]$$

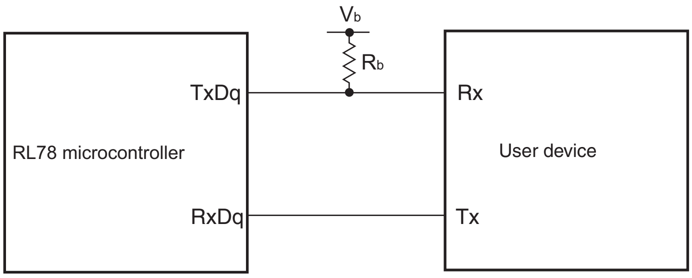
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

UART mode connection diagram (during communication at different potential)



(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		kHz
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		kHz
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		kHz
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		kHz
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		kHz
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.

2. Use it with EV_{DD0} ≥ V_b.

3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

	Reference Voltage		
Input channel	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI14	Refer to **2.6.1 (1)**.	Refer to **2.6.1 (3)**.	Refer to **2.6.1 (4)**.
ANI16 to ANI26	Refer to **2.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **2.6.1 (1)**.		–

(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]			±0.50	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AVREFP ≤ 5.5 V [Note 4]			±0.50	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]			±5.0	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]			±2.0	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

(**Notes** are listed on the next page.)

LVD Detection Voltage of Interrupt & Reset Mode

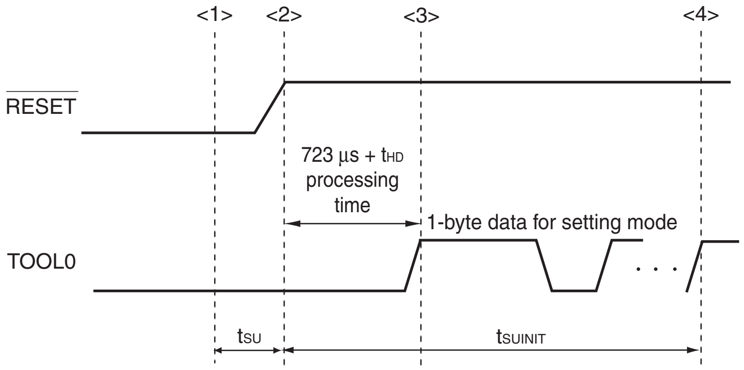
(T_A = –40 to +85°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDA0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 0, falling reset voltage			1.60	1.63	1.66	V
	V_{LVDA1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVDA2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVDA3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDB0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 1, falling reset voltage			1.80	1.84	1.87	V
	V_{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 0, falling reset voltage			2.40	2.45	2.50	V
	V_{LVDC1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDC3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 1, falling reset voltage			2.70	2.75	2.81	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

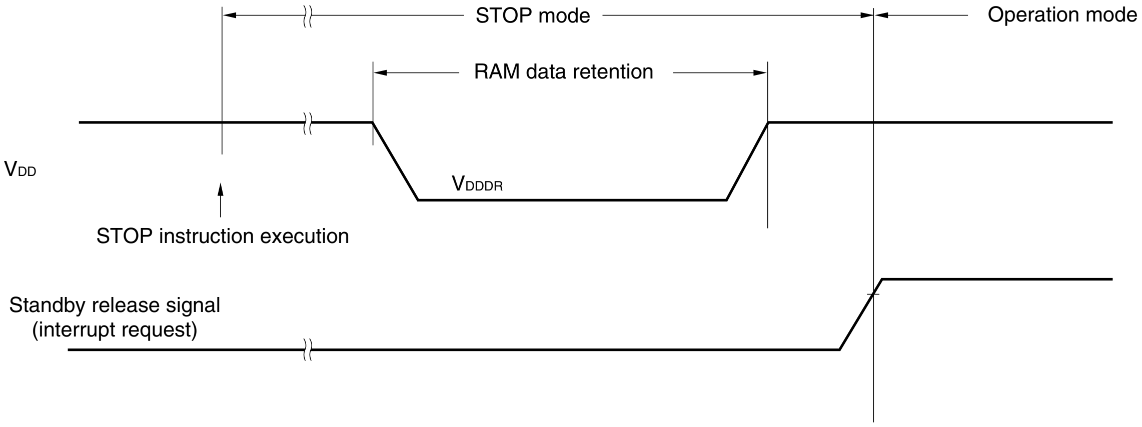
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

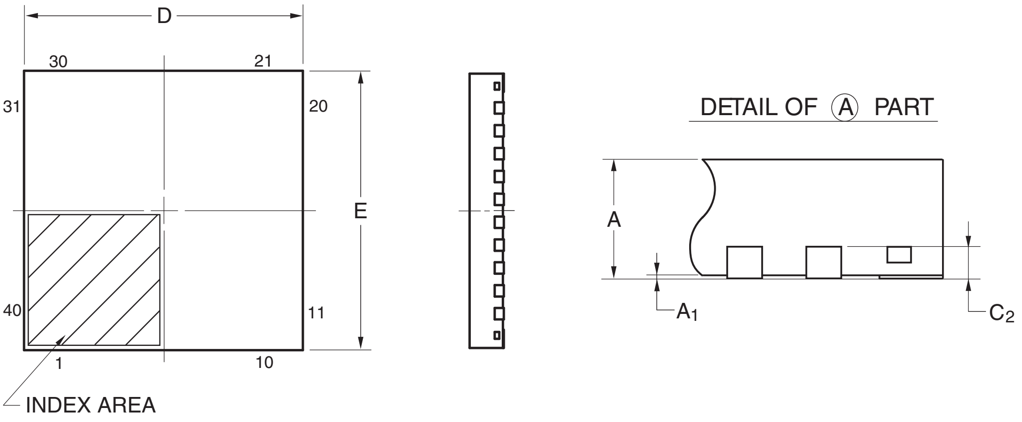
Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

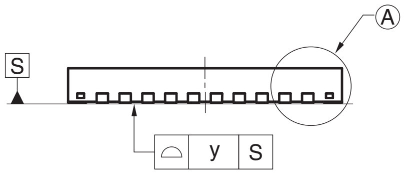


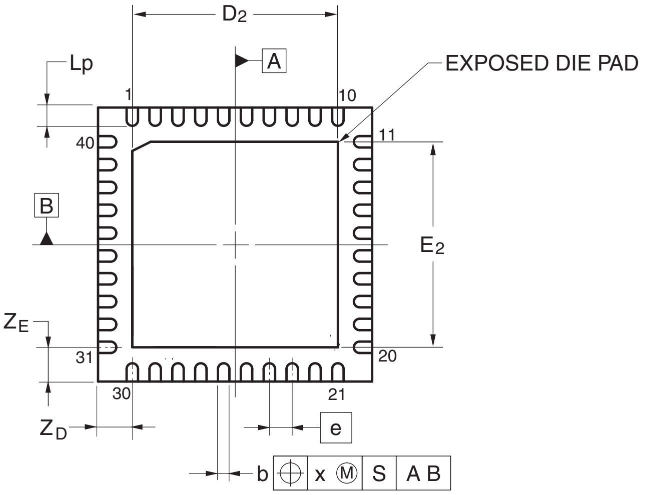
4.7 40-pin Products

R5F100EAANA, R5F100ECANA, R5F100EDANA, R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA
R5F101EAANA, R5F101ECANA, R5F101EDANA, R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA
R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA, R5F100EHDNA
R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA, R5F101EHDNA
R5F100EAGNA, R5F100ECGNA, R5F100EDGNA, R5F100EEGNA, R5F100EFGNA, R5F100EGGNA, R5F100EHGNA

JEITA Package code	**RENESAS code**	**Previous code**	**MASS (TYP.) [g]**
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09







Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	5.95	6.00	6.05
E	5.95	6.00	6.05
A	—	—	0.80
A_1	0.00	—	—
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05
Z_D	—	0.75	—
Z_E	—	0.75	—
c_2	0.15	0.20	0.25
D_2	—	4.50	—
E_2	—	4.50	—

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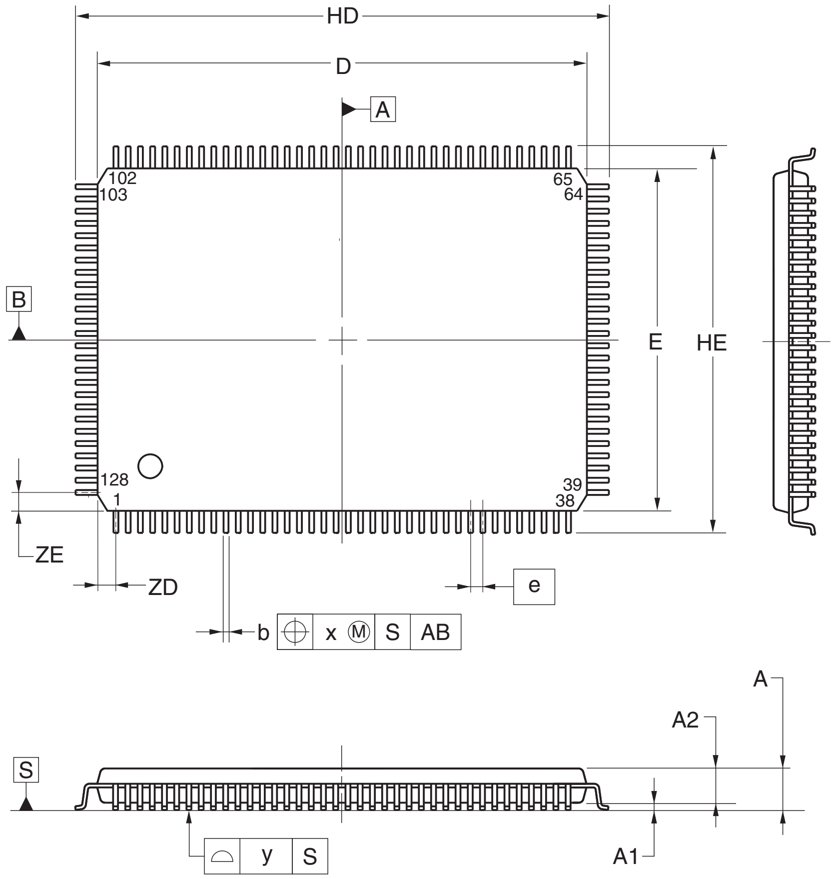
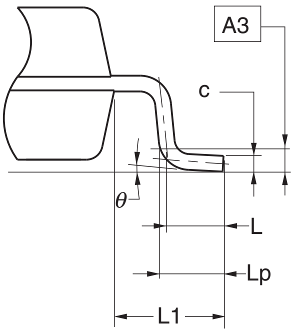
4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB
R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB
R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB
R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3°^{+5°}_{-3°}$
e	0.50
x	0.08
y	0.08
ZD	0.75
ZE	0.75

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NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.